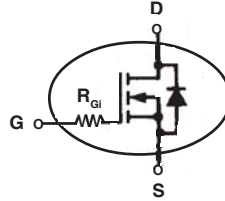


Linear L2™ Power MOSFET with extended FBSOA

N-Channel Enhancement Mode

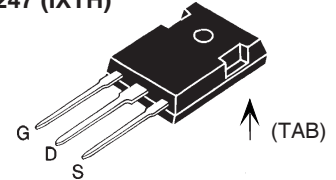
IXTH30N50L2
IXTQ30N50L2
IXTT30N50L2

V_{DSS} = 500V
I_{D25} = 30A
R_{DS(on)} ≤ 200mΩ

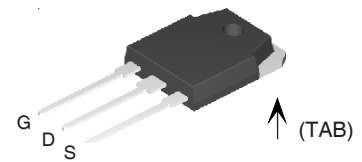


Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	500	V
V _{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	500	V
V _{GSS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	30	A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	60	A
I _{AR}	T _C = 25°C	30	A
E _{AR}	T _C = 25°C	50	mJ
E _{AS}		1.5	J
P _D	T _C = 25°C	400	W
T _J		-55 to +150	°C
T _{JM}		+150	°C
T _{stg}		-55 to +150	°C
T _L	1.6mm (0.063in) from case for 10s	300	°C
T _{SOLD}	Plastic body for 10s	260	°C
M _d	Mounting torque (TO-247, TO-3P)	1.13/10	Nm/lb.in.
Weight	TO-247	6.0	g
	TO-3P	5.5	g
	TO-268	5.0	g

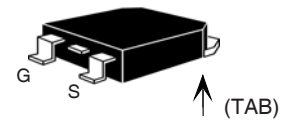
TO-247 (IXTH)



TO-3P (IXTQ)



TO-268 (IXTT)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- Designed for linear operation
- International standard packages
- Unclamped Inductive Switching (UIS) rated.
- Molding epoxies meet UL 94 V-0 flammability classification
- Integrated gate resistor for easy paralleling
- Guaranteed FBSOA at 75°C

Applications

- Solid state circuit breakers
- Soft start controls
- Linear amplifiers
- Programmable loads
- Current regulators

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
(T _J = 25°C, unless otherwise specified)				
BV _{DSS}	V _{GS} = 0V, I _D = 250μA	500		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.5		4.5 V
I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V			±100 nA
I _{DSS}	V _{DS} = V _{DSS}			50 μA
	V _{GS} = 0V T _J = 125°C			300 μA
R _{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1			200 mΩ

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
(T _J = 25°C, unless otherwise specified)					
g_{fs}	V _{DS} = 10V, I _D = 0.5 • I _{D25} , Note 1	9	12	15	S
C_{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		8100		pF
C_{oss}			530		pF
C_{rss}			115		pF
R_{Gi}	Integrated gate input resistor		3.5		Ω
t_{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 0Ω (External)		35		ns
t_r			117		ns
t_{d(off)}			94		ns
t_f			40		ns
Q_{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		240		nC
Q_{gs}			58		nC
Q_{gd}			135		nC
R_{thJC}				0.31	°C/W
R_{thCS}	(TO-247, TO-3P)		0.25		°C/W

Safe Operating Area Specification

Symbol	Test Conditions	Min.	Typ.	Max.
SOA	V _{DS} = 400V, I _D = 0.5A, T _C = 75°C, t _p = 2s	200		W

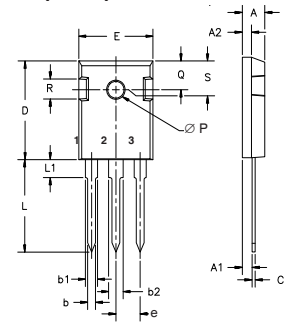
Source-Drain Diode

Characteristic Values
(T_J = 25°C, unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
I_s	V _{GS} = 0V			30 A
I_{SM}	Repetitive, pulse width limited by T _{JM}			120 A
V_{SD}	I _F = I _S , V _{GS} = 0V, Note 1			1.5 V
t_{rr}	I _F = I _S , -di/dt = 100A/μs, V _R = 100V		500	ns

Note 1: Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

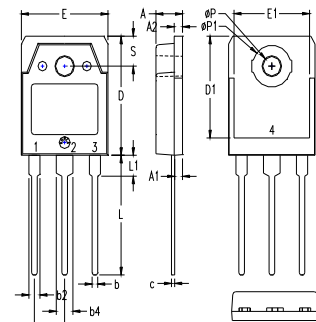
TO-247 (IXTH) Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
∅P	3.55	3.65	.140	.144
∅P1	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

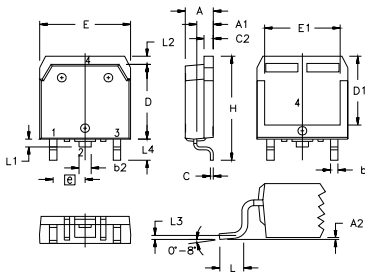
TO-3P (IXTQ) Outline



1 - GATE
2 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)
4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A ₁	.051	.059	1.30	1.50
A ₂	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b ₂	.075	.087	1.90	2.20
b ₄	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D ₁	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E ₁	.531	.539	13.50	13.70
e		.215 BSC		5.45 BSC
L	.779	.795	19.80	20.20
L ₁	.134	.142	3.40	3.60
∅P	.126	.134	3.20	3.40
∅P1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

TO-268 (IXTT) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e		.215 BSC		5.45 BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃		.010 BSC		0.25 BSC
L ₄	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics
@ $T_J = 25^\circ\text{C}$

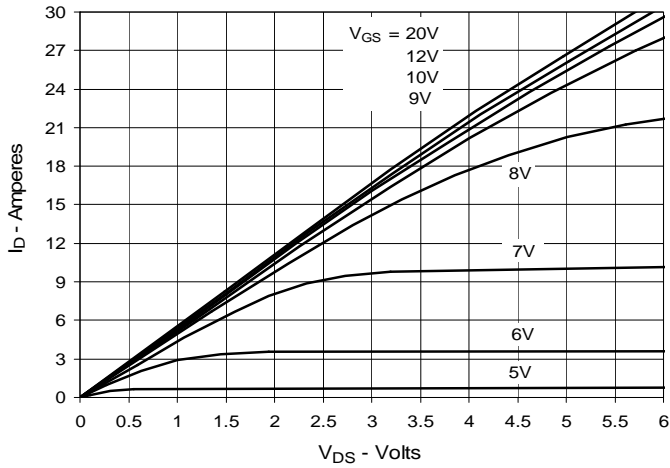


Fig. 2. Extended Output Characteristics
@ $T_J = 25^\circ\text{C}$

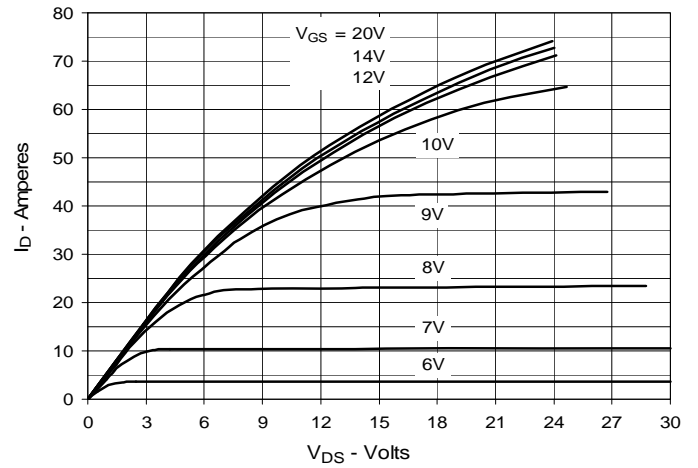


Fig. 3. Output Characteristics
@ $T_J = 125^\circ\text{C}$

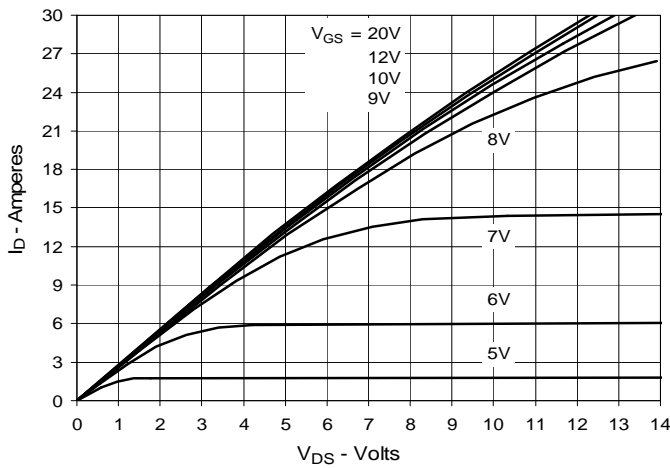


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 15\text{A}$ Value vs. Junction Temperature

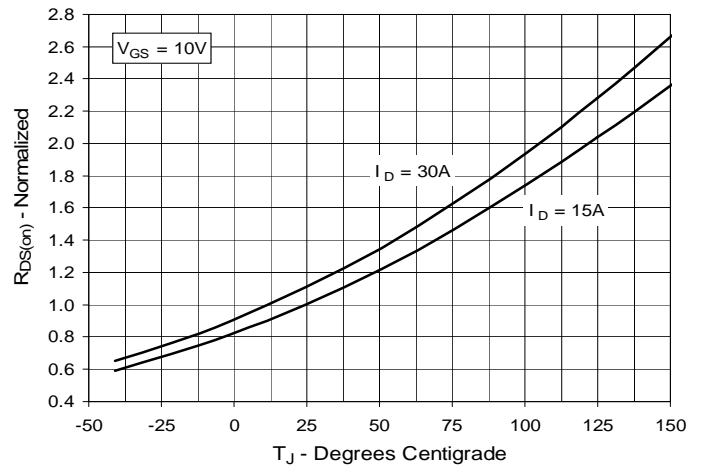


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 15\text{A}$ Value vs. Drain Current

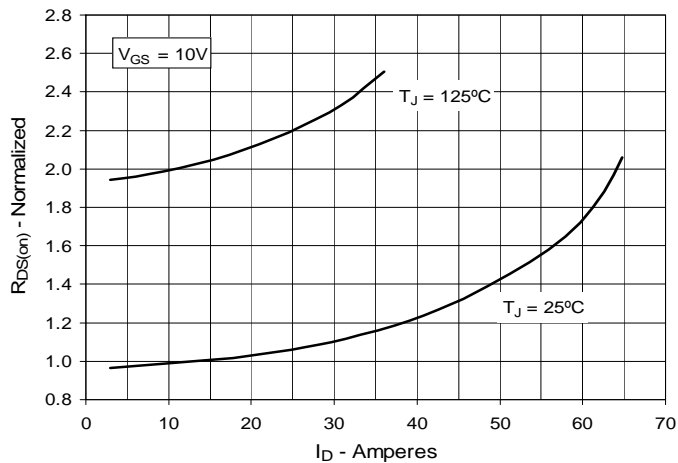


Fig. 6. Maximum Drain Current vs. Case Temperature

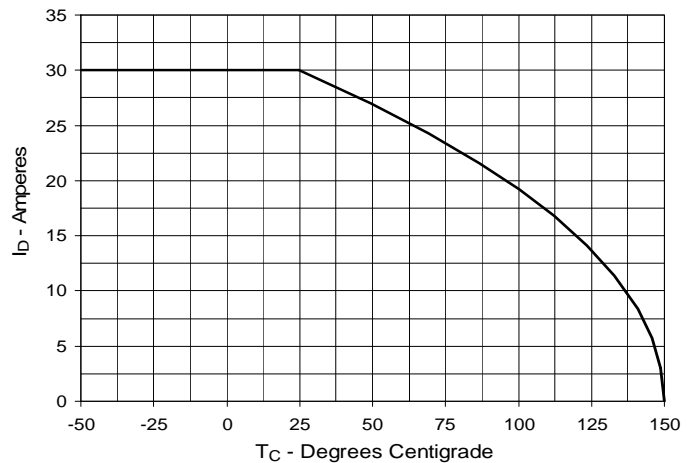


Fig. 7. Input Admittance

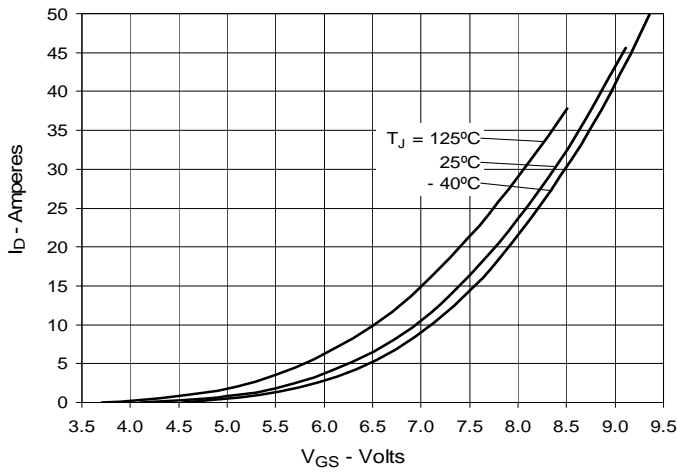


Fig. 8. Transconductance

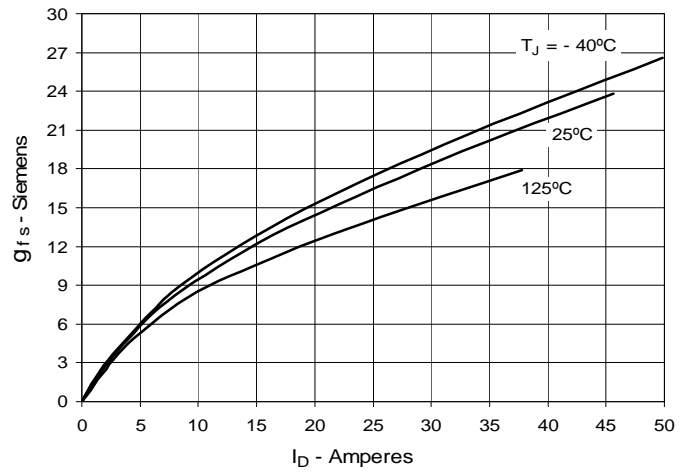


Fig. 9. Forward Voltage Drop of Intrinsic Diode

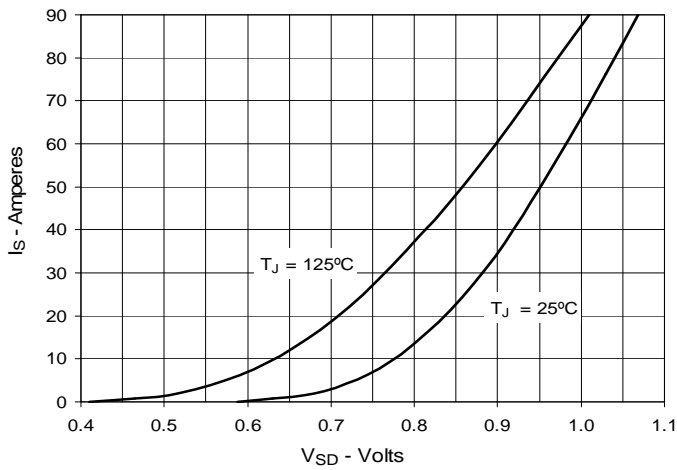


Fig. 10. Gate Charge

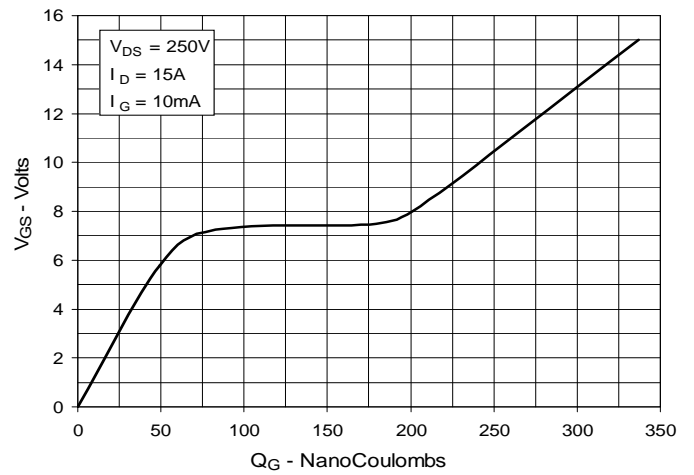


Fig. 11. Capacitance

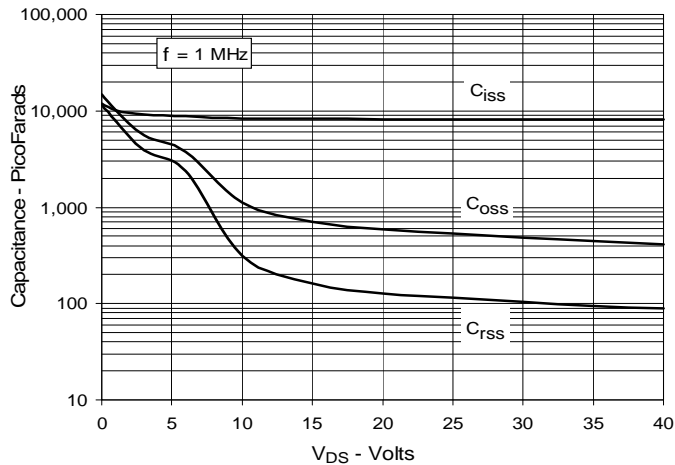


Fig. 12. Maximum Transient Thermal Impedance

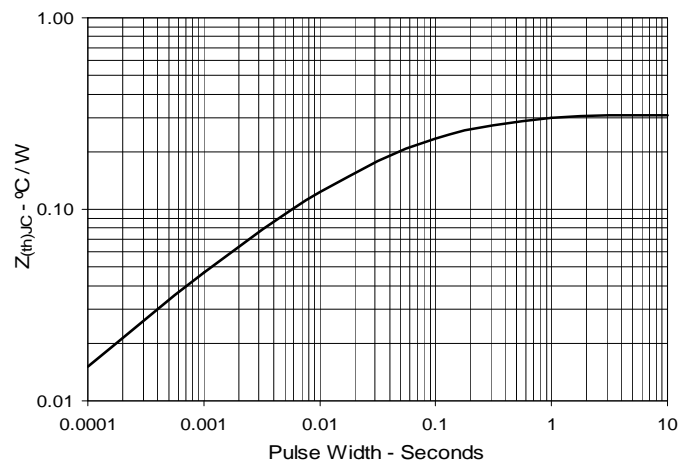


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

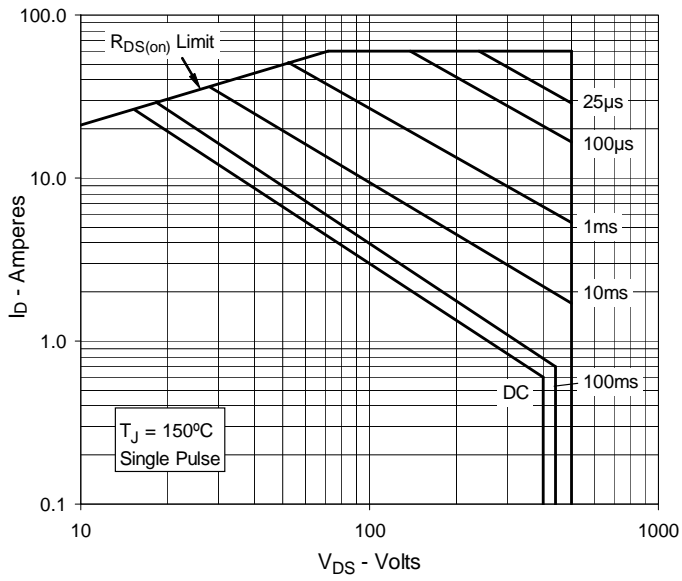


Fig. 14. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$

